



HCP2269 Specification

Features

- | Proprietary frequency shuffling technology for improved EMI performance.
- | External programmable PWM switching frequency.
- | Leading edge Blanking on current sense input.
- | Internal synchronized slope compensation .
- | Extended burst mode control for improved efficiency and minimum standby power design
- | Low VDD startup current and low operating current.
- | Gate output maximum voltage clamp 18V.
- | Cycle-by-Cycle Current Limiting, Built-in Adaptive Current Peak Regulation
- | Power on Soft-start, Programmable CV and CC Regulation
- | VDD Under Voltage Lockout with Hysteresis(UVLO),VDD OVP, VDD Clamp

Applications

- | Digital Cameras Charger
- | Power adaptor
- | Set_top box power supplies
- | Open_frame SMPS
- | Battery charger

Description

HCP2269 is highly integrated current mode PWM control IC optimized for high performance, low standby power and cost effective offline flyblack converter applications in sub 80W range.

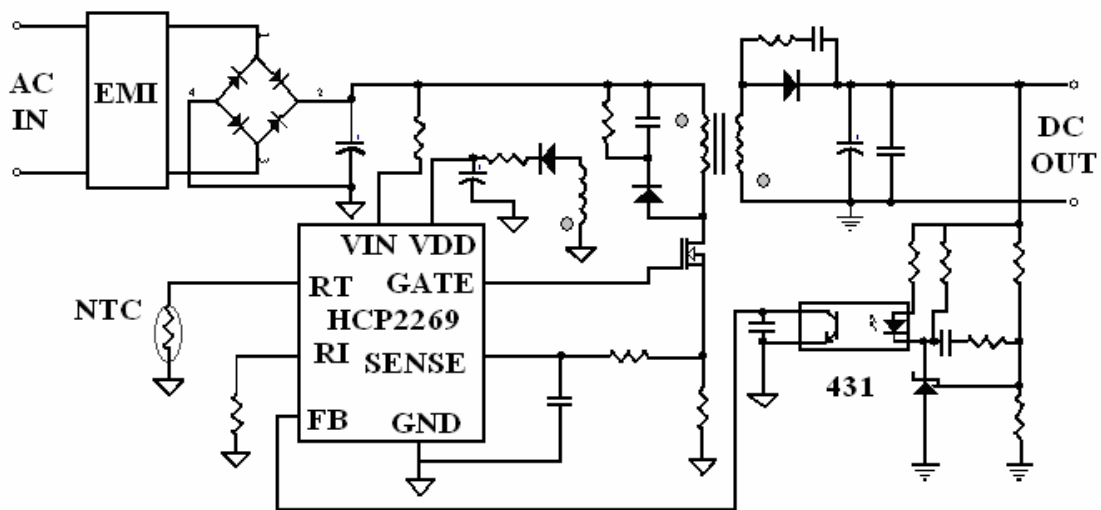
PWM switching frequency at normal operation is externally programmable to tight range. At no load or light load condition, the IC operates in extended ‘burst mode’ to minimize switching loss.Lower standby power and higher conversion efficiency in thus achieved.



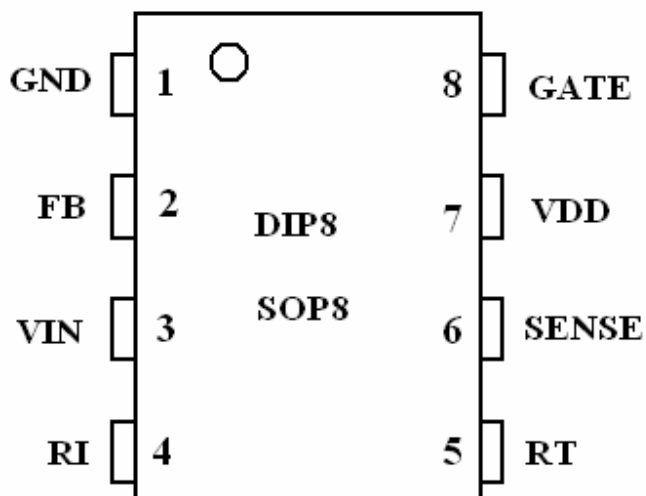
VDD low startup current and low operating current contribute to a reliable power on startup design with HCP2269. A large value resistor could thus be used in the startup circuit to minimize the standby power.

HCP2269 offers complete protection coverage with automatic self-recovery feature including Cycle-by-Cycle current limiting(OCP), over temperature protection(OTP), VDD over voltage clamp and under voltage lockout (UVLO). The Gate output is clamped to maximum 18V to protect the power MOSFET.

Application Circuit



Pin Assignment (DIP8,SOP8)





Pin Description

Symbol	Type	Description
GATE	O	Totem-pole gate driver output for the power MOSFET
VDD	P	Chip DC power supply pin
SENSE	I	Current sense input pin. Connected to MOSFET current resistor node.
RI	I	Internal oscillator frequency setting pin.
FB	I	Feedback input pin. The PWM duty cycle is determined by voltage level into this pin and SENSE pin input.
Gnd	P	Ground.
RT	I	Temperature sensing input pin, connected through a NTC resistor to GND.
VIN	I	Connected through a large value resistor to rectified line input for startup IC supply GND and line voltage sensing.

Absolute Maximum Rating

Parameter	Value	Unit
VDD/VIN supply voltage	30	V
VDD zener clamp voltage	VDD clamp +0.1	K Ω
VDD clamp continuous current	10	mA
VFB input voltage	-0.3 to 7	V
VSENSE input voltage to SENSE pin	-0.3 to 7	V
VRT input voltage to RT pin	-0.3 to 7	V
VRI input voltage to RI pin	-0.3 to 7	V
Operating ambient temperature	-20 to 85	°C
Min/Max operating junction temperature	-55 to 150	°C



Technical Specifications

Symbol	Parameter	Conditions	Value			Unit
			Min.	Typ.	Max	
I _{dd_startup}	VDD start up current	VDD=12.5V RI=24K		3	10	uA
I _{dd}	VDD current	VDD=18V RI=24K Ω , FB=3.6V		2.3		mA
UVLO (enter)	VDD under voltage lockout enter		9.5	10.5	11.5	V
UVLO(exit)	VDD under voltage lockout exit		15.5	16.5	17.5	V
OVP(enter)	VDD over voltage protection enter		27	28	29	V
OVP(exit)	VDD over voltage protection exit		25	26	27	V
VDD_clamp p	VDD zener clamp voltage	I _{dd} =10mA	29	30	31	V
T _{D_OVP}	VDD OVP debounce time			80		uS
AVCS	PWM input gain	$\Delta V_{FB} / \Delta V_{SENSE}$		2.8		V/V
V _{FB_open}	V _{FB} open loop voltage			5.3		V
I _{FB_short}	FB pin short current	Short FB pin to GND and measure current		0.9		mA
V _{TH_PL}	Power limiting FB threshold voltage	I _{out} =-10mA		4.4		V
T _{D_PL}	Power limiting debounce time			64		mS
DC_MAX	Maximum duty cycle	VDD=18V, FB=3V SENSE=0V		80		%
T _{blanking}	Leading edge blanking time			250		nS



ZSENSE_IN	Input impedance			30		K Ω
VTH_OC_0	Current limiting threshold voltage at no compensation	I(VIN)= 0 μ A		0.9		V
VTH_OC_1	Current limiting threshold voltage at compensation	I(VIN)= 150 μ A		0.81		V
Fosc	Normal oscillation frequency	RI=24K Ω	60	65	70	Khz
Δf_{temp}	Frequency temperature stability	TA -20 $^{\circ}$ C to 100 $^{\circ}$ C VDD=16V,RI=24K Ω		2		%
Δf_{VDD}	Frequency voltage stability	VDD=12V to 25V RI=24K Ω		2		%
RI_range	Operating RI range		12	24	60	K Ω
VRI_open	RI open load voltage			2		V
Fosc_BM	Burst mode base frequency			22		Khz
Δf_{OSC}	Frequency modulation range /Base frequency		-3		+3	%
VOL	Output low level	VDD=18V,IO=-20mA			0.3	V
VOH	Output high level	VDD=18V,IO=20mA	11			V
V_Clamp	output clamp voltage level			18		V
T_r	Output rising time	VDD=18V,CL=1nF		110		nS
T_f	Output falling time	VDD=18V,CL=1nF		40		nS
I_RT	Output current of RT pin			70		μ A
V_OTP	OTP threshold voltage		1	1.05	1.1	V
V_OTP_off	OTP recovery threshold voltage			1.15		V
T_OTP	OTP de-bounce time			100		μ S